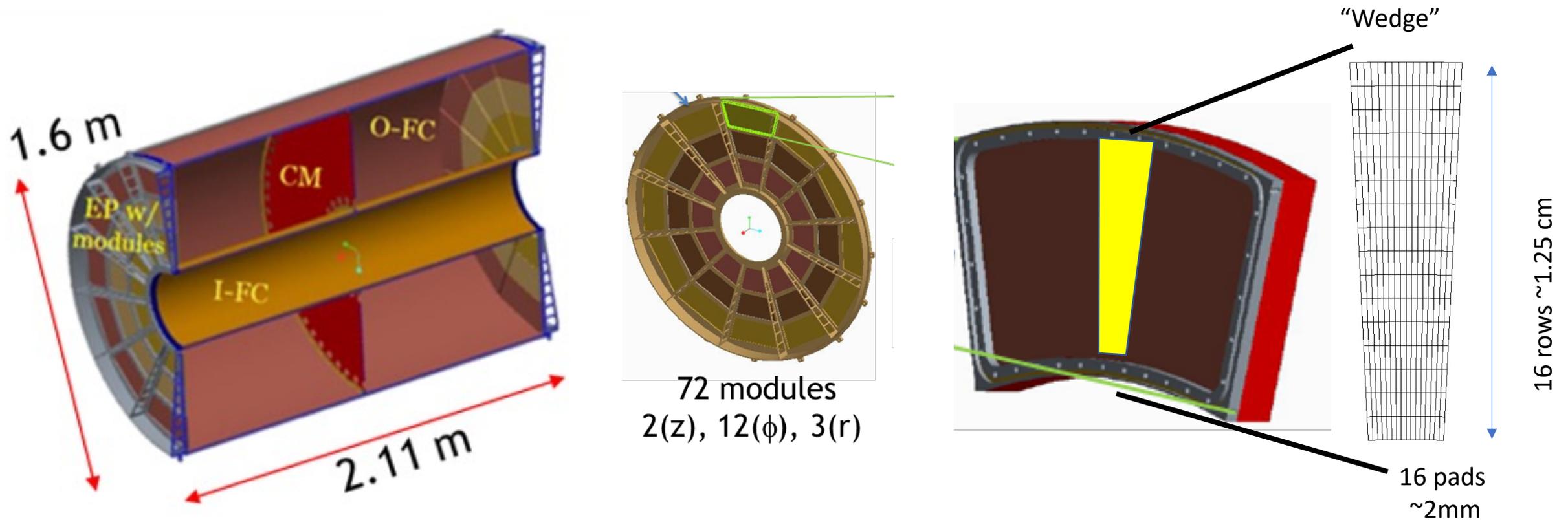


Latest status of SAMPA v5 in sPHENIX TPC

Takao Sakaguchi
Brookhaven National Laboratory

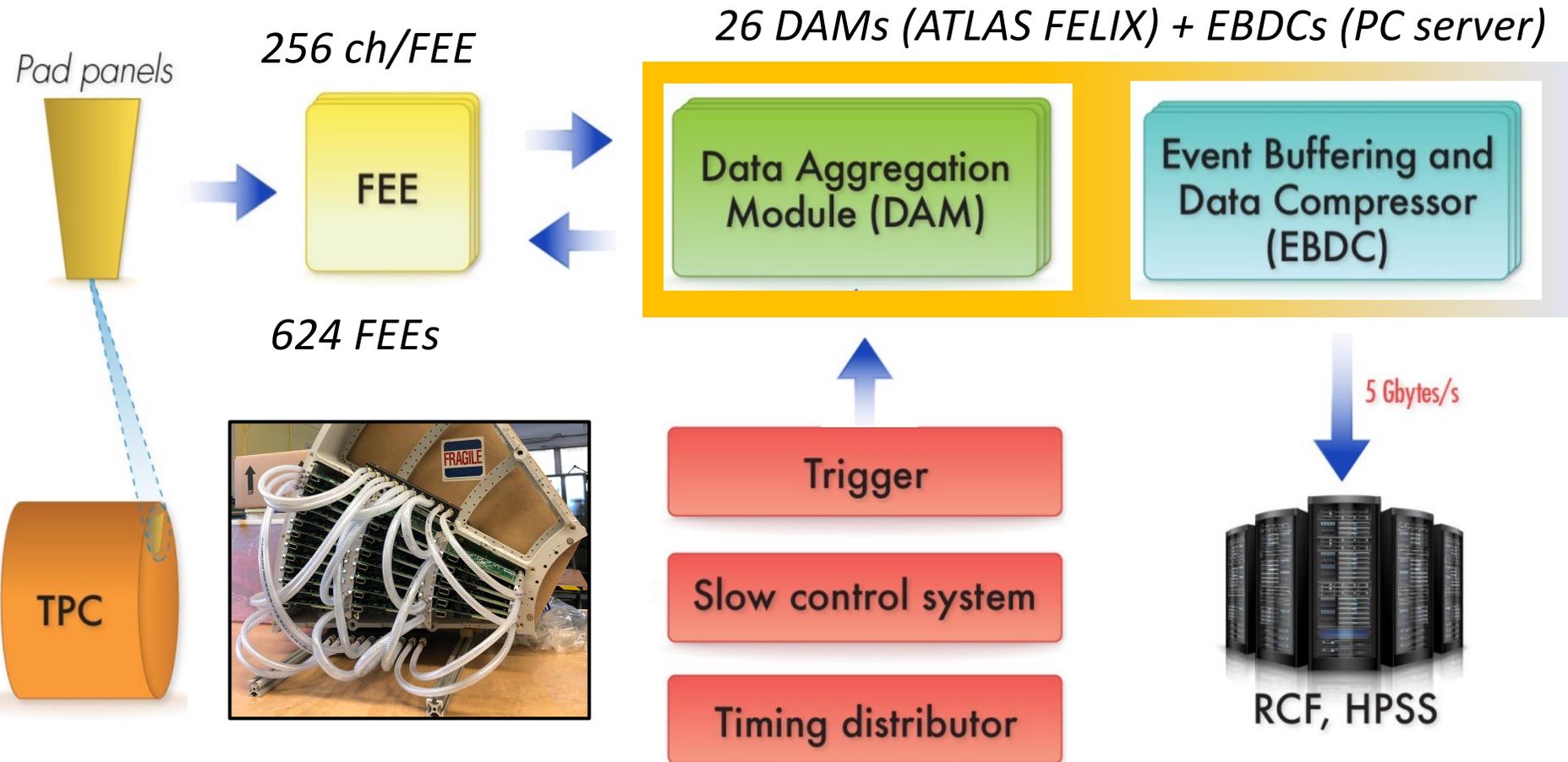
SPHENIX TPC

- Primary device for tracking and momentum measurement
- Fiducial volume: $20 < r < 80 \text{ cm}$, full azimuth, $|\eta| < 1.1$ (@ $r=80 \text{ cm}$)
- Event rate: $\sim 15\text{-}100 \text{ kHz}$ ($\sqrt{s_{NN}}=200 \text{ GeV}$, Au+Au collisions)
- Goal is to achieve $100\text{-}150 \mu\text{m}$ position resolution in the fiducial volume



sPHENIX TPC readout system

- Overall readout scheme: padplane -> FEE -> DAM+EBDC -> Storage
- Data rate: ~10Mbits per Au+Au MB events from whole TPC



Total # of FEEs is 624

of FEEs per sector:

6 for $20 < r < 40\text{cm}$

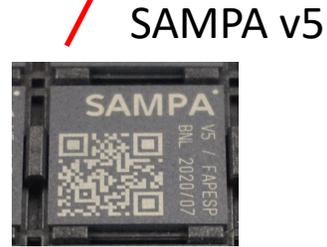
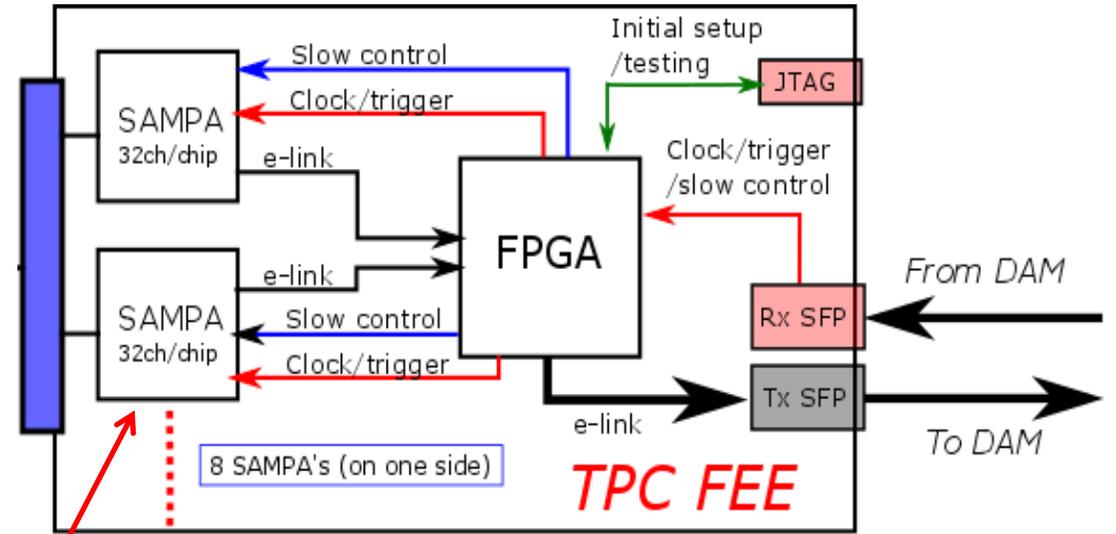
8 for $40 < r < 60\text{cm}$

12 for $60 < r < 78\text{cm}$

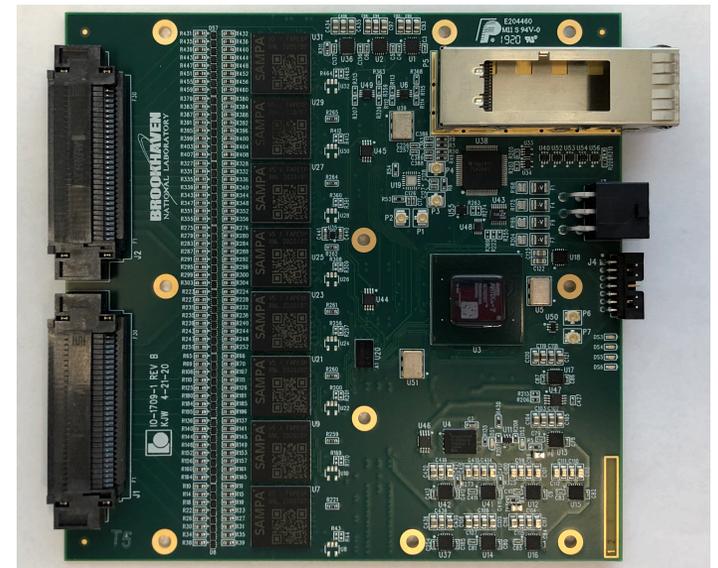
$1 \text{ sector} = 2\pi/12 \text{ per side}$

Front End Electronics (FEE)

- **Continuous readout mode**
- Use of 8 SAMPA chips per FEE (256ch/FEE)
- Use of newly developed SAMPA v5 that has 80nsec shaping time option.
 - 160nsec is also available
- FPGA receives data from SAMPA and sends to optical link, and processes clock and slow control data from DAM.
 - JTAG is implemented over optical link.
 - Two data links are available
- ADC clock will be 4.7, 9.4 or 18.8 MHz, as we base on the RHIC beam-crossing clock.
- Power consumption: ~15W per card



Pre-production FEE board →

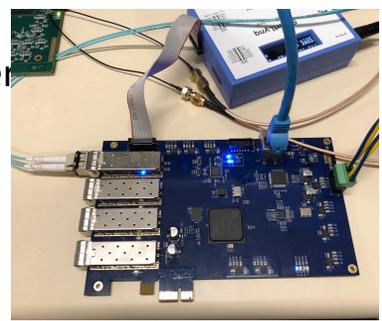
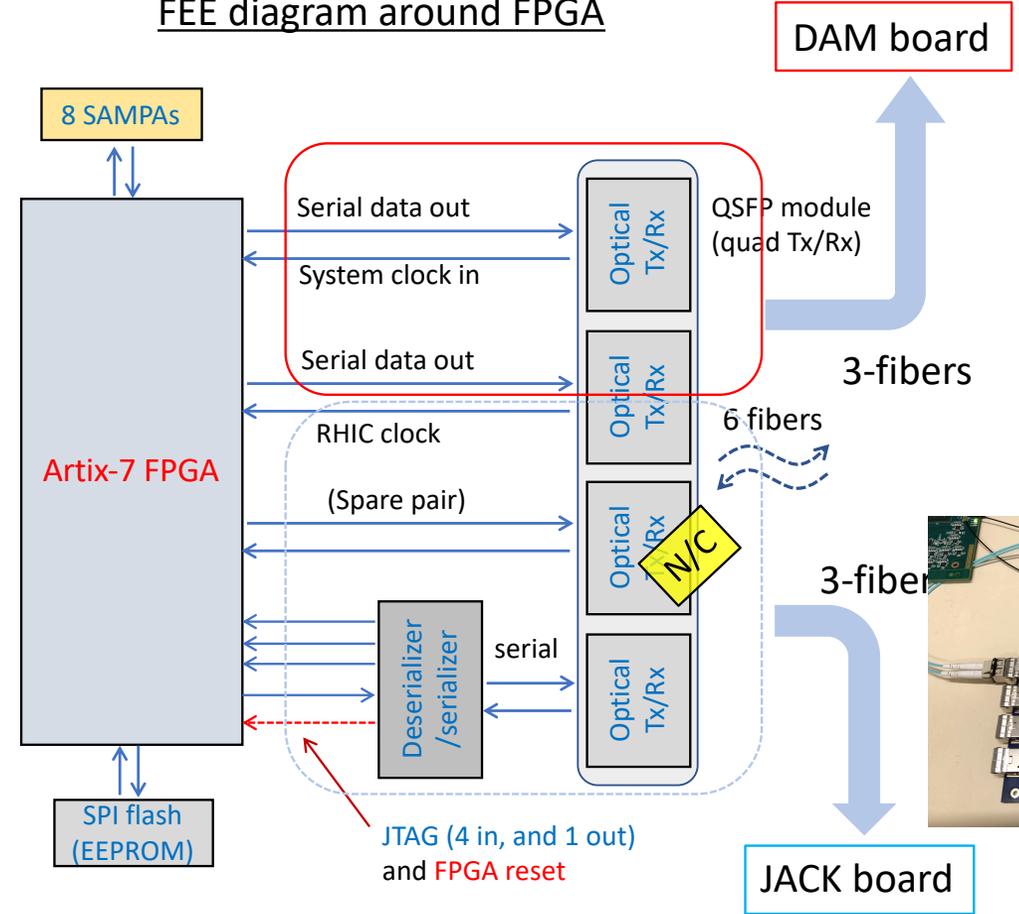


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FEE diagram around FPGA



SAMPA chip feature (v4)

- SAMPA = 32 ch * (CSA + Shaper + FADC) + DSP
- CSA (pos/neg input) + Shaper: see table
- FADC (10bits) sampling: 5, 10, and 20MHz.
- DSP functions:
 - Data buffering and packeting (header etc.)
 - Three baseline correction (restoration) schemes
 - Data reduction schemes are simple zero-suppression (ZS), cluster-sum after ZS applied, and Huffman compression (Never used)
- Operation mode
 - Triggered and trigger-less (continuous) readout mode
 - Direct ADC serialization
- Output: 11 e-links per chip.
 - 320Mbps per line → 3.2Gbps per chip
 - 10MHz sampling without zero-suppression is possible
- Good literatures:
 - https://readthedocs.web.cern.ch/ate/files/119245990/148606571/2/1592314724000/Sampa_V4_DataSheet.pdf
 - ALICE paper: <https://doi.org/10.1088/1748-0221/16/03/P03022>

Gain	Shaping time
30 mV/fC	160 ns
20 mV/fC	160 ns
4 mV/fC	300 ns

Power: ~1W per chip

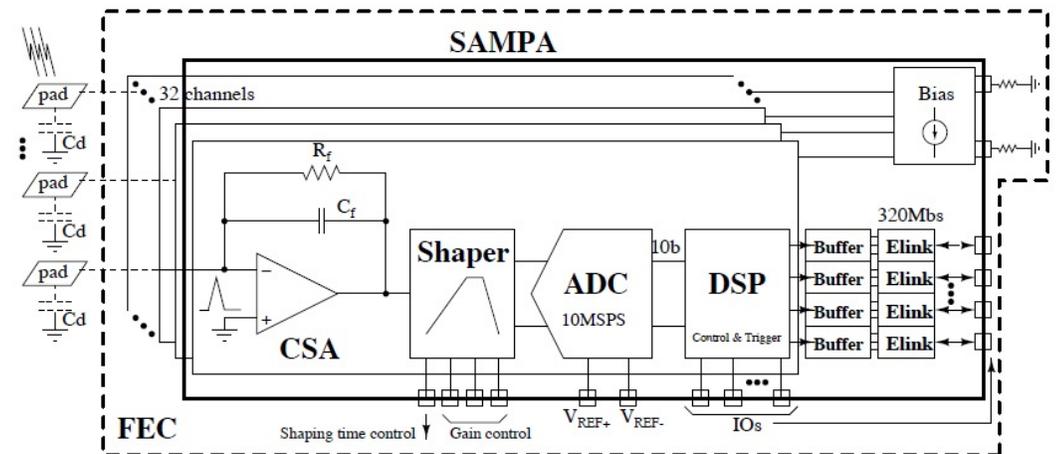


Figure 6.4: Schematic of the SAMPA ASIC for the GEM TPC readout, showing the main building blocks.

SAMPA overall history

- MPW1 (multi-project wafer) is SAMPA “components”
 - 80, 160 and 300nsec shaping times were tested.
- MPW2 was the first integrated SAMPA chip
 - 80nsec was already dropped here.
- MWP3 (or SAMPA v3) was supposed to be the “production version” ...
 - DSP issue was fixed, and pedestal memory part was redesigned to mitigate radiation issue.
 - Submitted for fabrication in early July 2017.
- MWP4 (or SAMPA v4) has shorter decay time for CSA (by changing R_f) for avoiding saturation by pile-up
 - Submitted for fabrication in early July 2017
- SAMPA v5 development for sPHENIX TPC from Apr 2018
 - Due to high hit occupancy in sPHENIX (Au+Au, 100KHz), shaping time faster than 160nsec was desired.
 - 80nsec shaping time is revived, in place of 300nsec
 - Modified FADC SAR switch for better ENOB

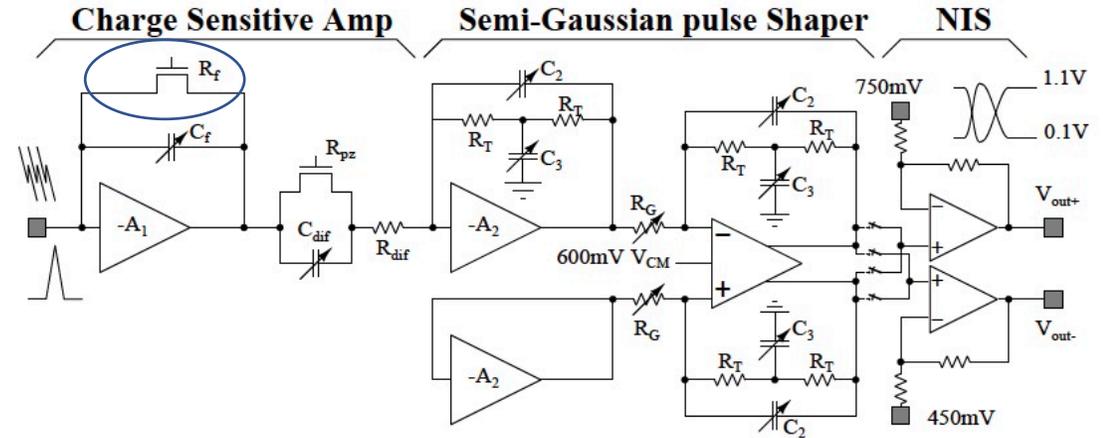
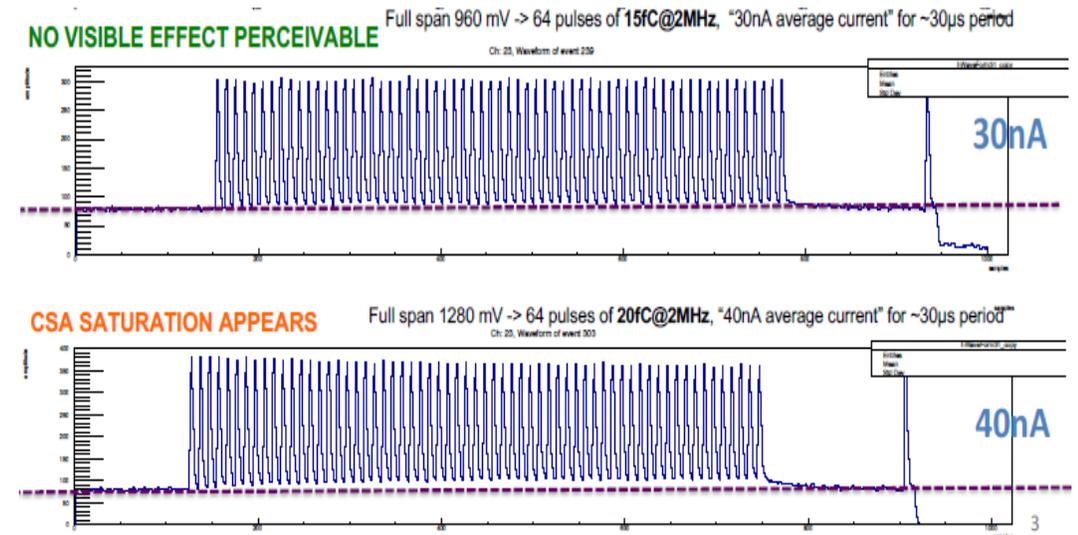


Figure 1.1: Block diagram of the analog front-end.



SAMPA v5 development history

- Simulation study started at U. Sao Paulo (USP) in Apr 2018
 - 80nsec shaping time revisited
- SAR ADC switching was also revised
 - Not implemented in v4 since the ENOB of ADC was already good for ALICE at that time.
 - Essential for 20MHz operation
- MPW design was submitted to TSMC in Oct, 2018
- MPW arrived at USP in Mar, 2019
 - Test was conducted by USP: Apr-Jun, 2019
 - At same time, the design of integrated chip (SAMPA v5) was performed.
- Full-chip production started Oct, 2019
 - First 4 wafers were delivered to USP and Lund in early Mar 2020 for initial testing.

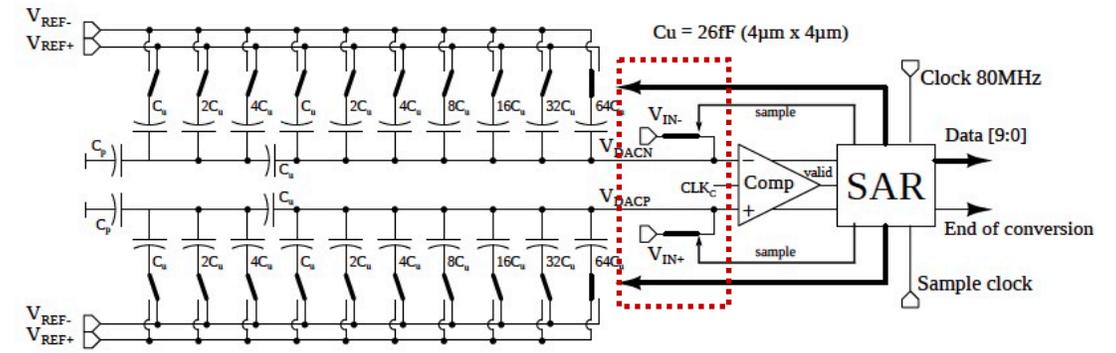
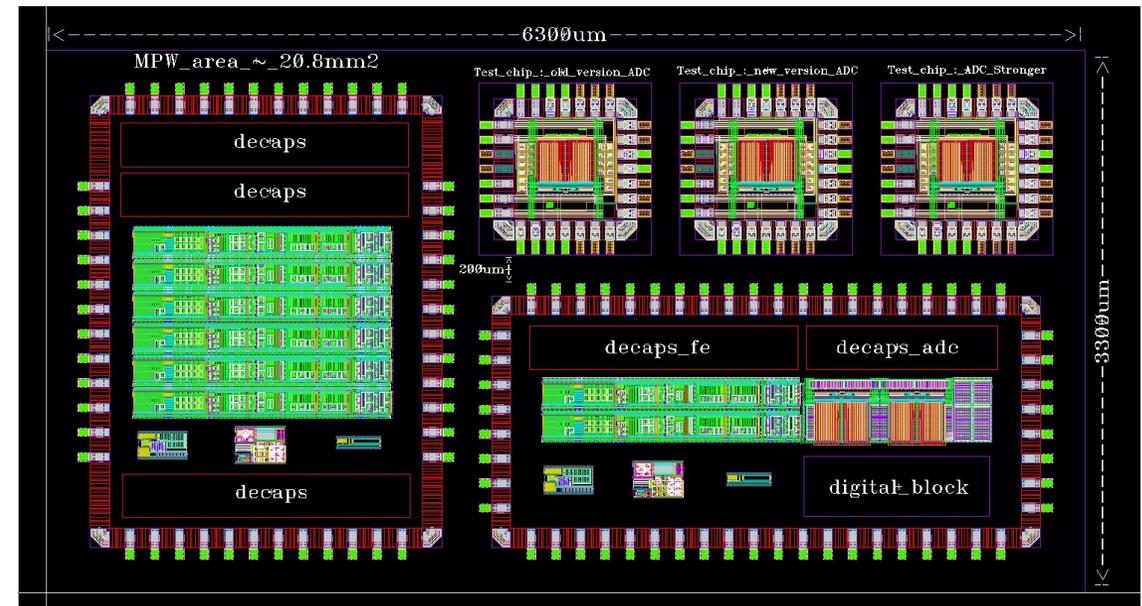


Figure 1.2: Block diagram of the ADC.



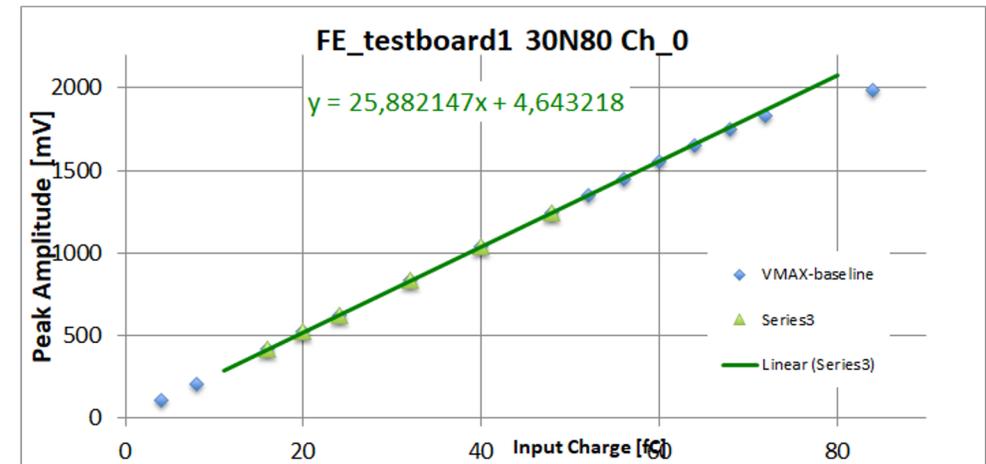
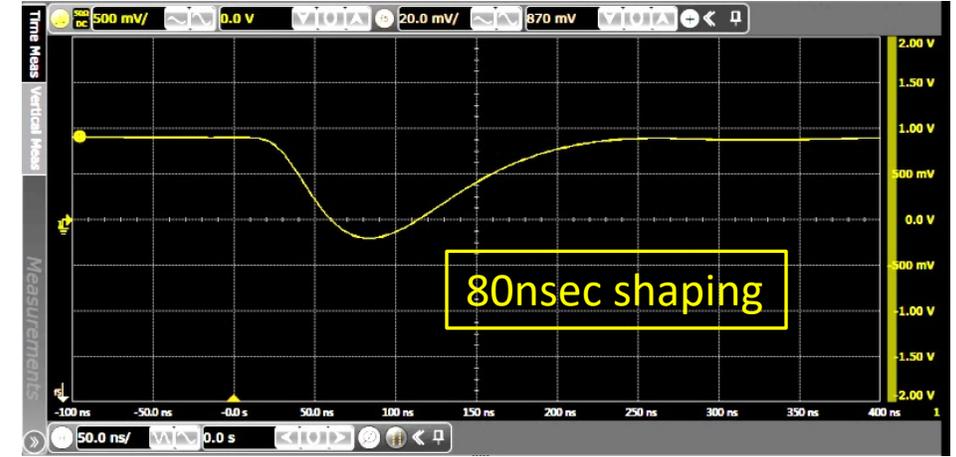
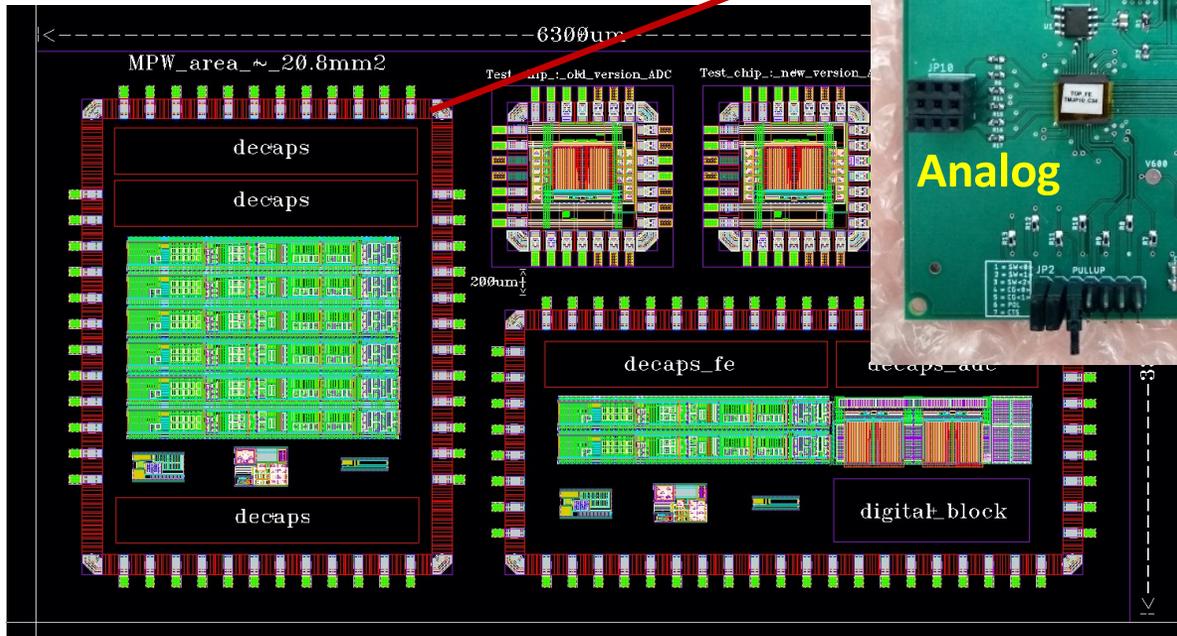
Test results from MPW chips (Analog)

- SAMPA v5 components were produced in a multi-project wafer (MPW) run
- Initial test shows a good linearity for 80nsec shaping and 30mV/fC gain.
 - Power consumption: 6mW/ch
 - Noise: $\sim 500e$ @ $C_{in}=0$, $\sim 600e$ @ $C_{in}=20pF$

1, Analog (CSA+Shaping) only

2, ADC only

3, Inclusive chain (Analog+ADC)

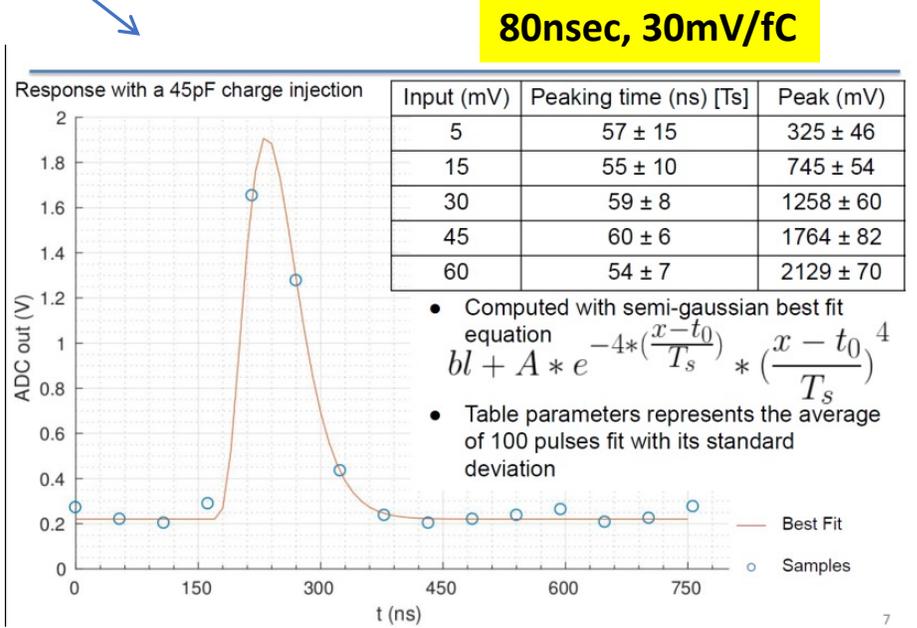
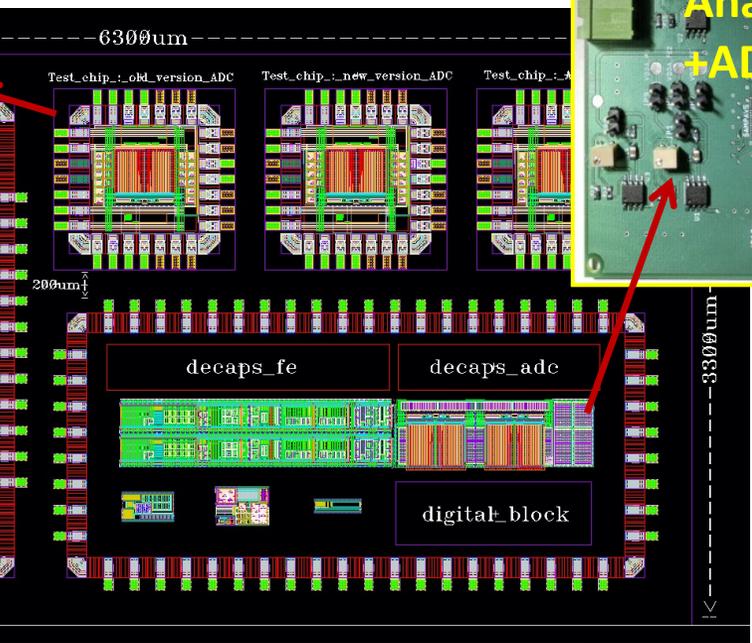
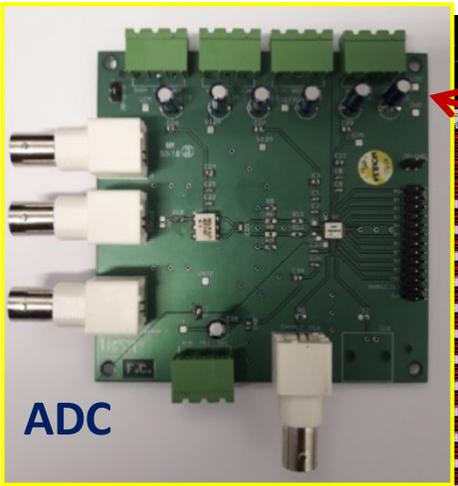


Test results from MPW chips (ADC)

- ADC and Analog+ADC components
- ENOB of ADC is found to be better than that of SAMPA v4
 - Improvement at 18MHz is seen and is close to expected
- Pulse shape is successfully measured by Analog+ADC

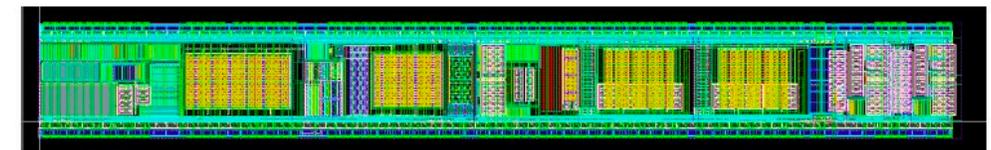
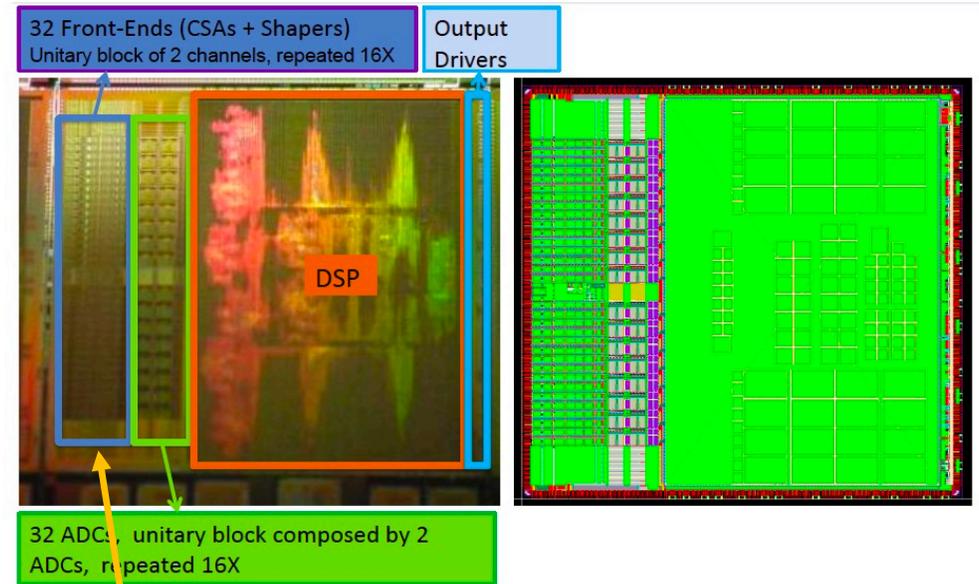
- 1, Analog (CSA+Shaping) only
- 2, ADC only
- 3, Inclusive chain (Analog+ADC)

	18.5 MSPs	
Amplitude (% of maximum)	ADC V4 ENOB (bits)	ADC V5 ENOB avg. (bits)
40	9.2	9.2
50	8.6	9.1
70	8.6	8.9
90	8.2	8.7

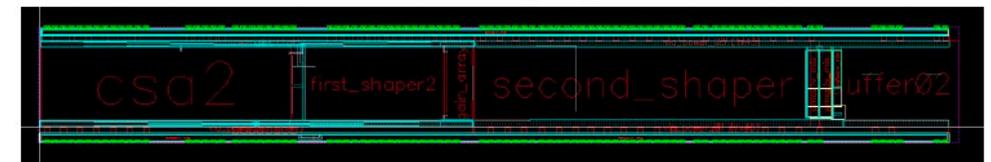


Production of SAMPA v5 chips

- New CSA, Shaper, and FADC circuits were integrated to the “SAMPA” chip
 - Layout were rechecked
- Produced wafers from so-called MLM maskset
- Total chips produced: ~12k
 - # of chips absolutely needed is 4992.
 - Chips per wafer is ~264
 - An engineering run produced 21 wafers: ~5500 chips
 - A production run gives 25 wafers: ~6600 chip
- Production history
 - Processed first 4 of 21 wafers to the final packaged chips (~1000 chips)
 - Rest 17 of 21 wafers were held at contact level
 - Proceed to packaging for the 17 wafers and run another 25 wafers after the 1000 chips were confirmed fine
- If you are interested in cost, ask offline.



New CSA_Shaper



Test results from production chips

- Detail test results from U. Sao Paulo
- Noise look somewhat larger than expected, due to noise from the test board
- Very good linearity was observed
- Peaking time is shorter than defined

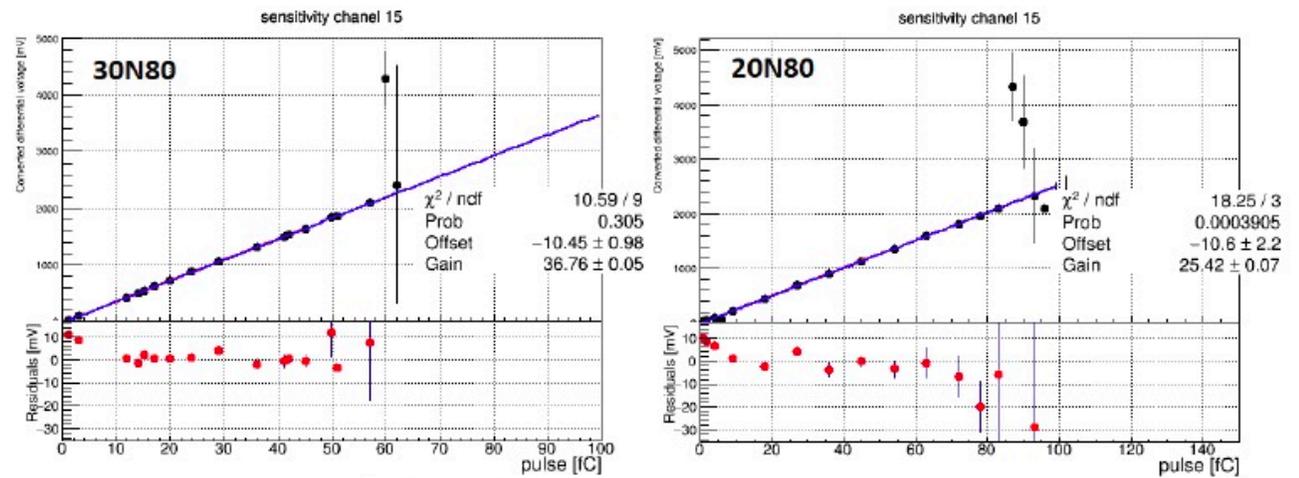
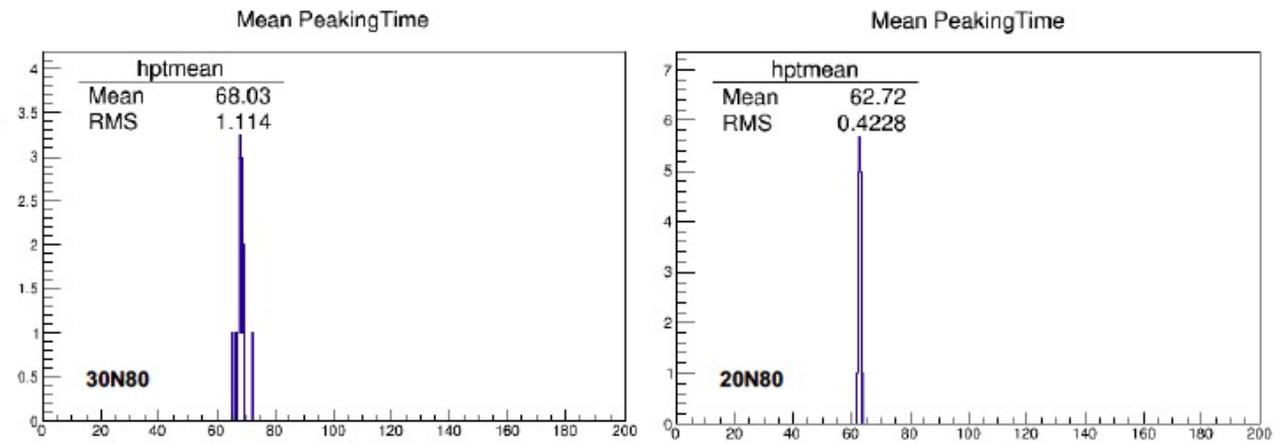
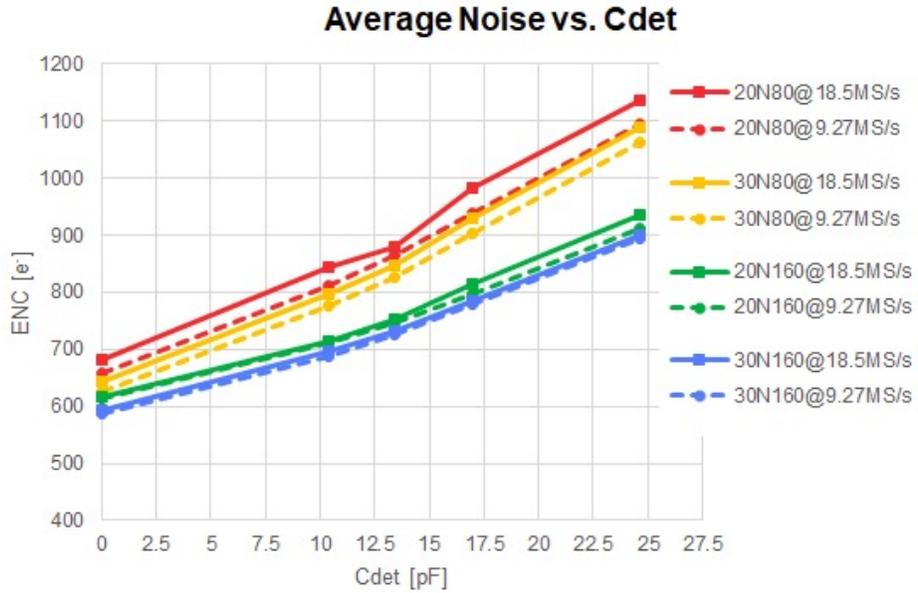


Figure 10.1: Sensitivity for one channel of sample 11 at 18.542 MS/s.

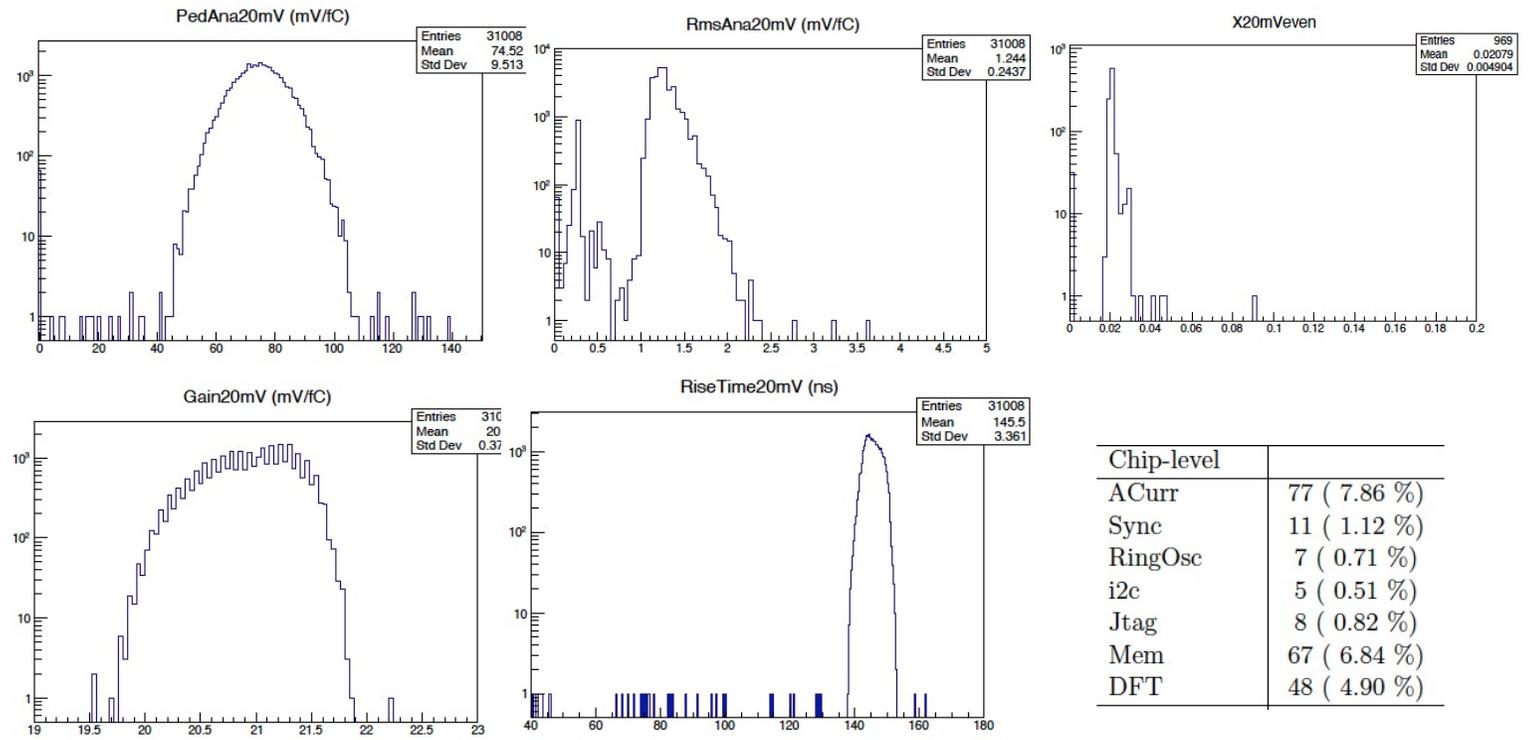


Mass chip testing at Lund University

- Robot testing stand was built at Lund University (Sweden) for ALICE. Lund joined sPHENIX lately
- Two pass testing: 160nsec and 80nsec. Same testing items as for ALICE TPC/MuCH
- SAMPA v5 test at 160nsec is finished. Yield is ~70%. 80nsec test in progress



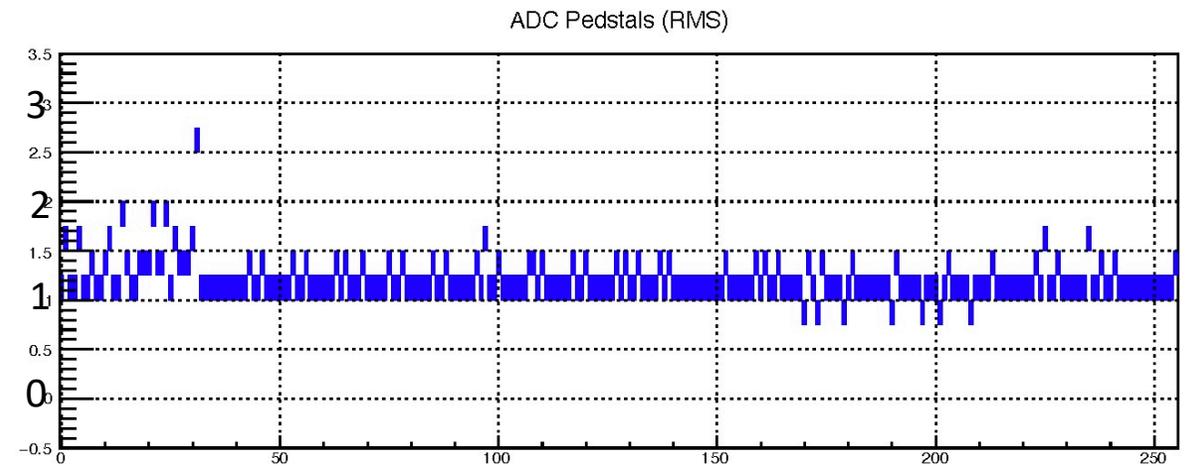
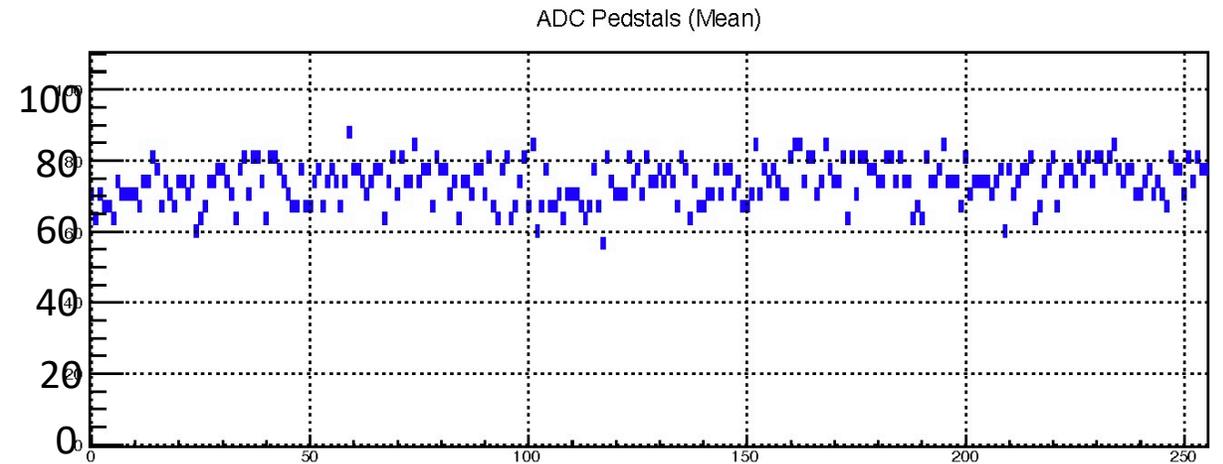
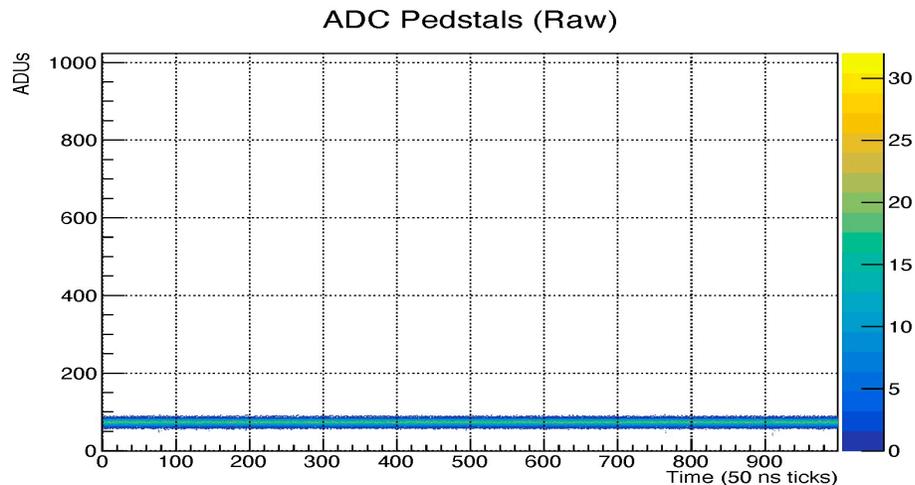
<https://youtu.be/3tnqPbMWzqQ>



Testing results at 160nsec shaping from the first 980 chips

SAMPA data from Pre-production FEE

- Pedestals of 256 channel output from the pre-production version of FEE cards
- No detector or capacitance to input ($C_{det}=0$)
- 80nsec shaping, 20mV/fC, 20MHz sampling
- No zero-suppression, no base-line correction
- RMS of ~ 1.2 ADU corresponding to $\sim 700 e$



channels

Plots made by John Kuczewski (IO)

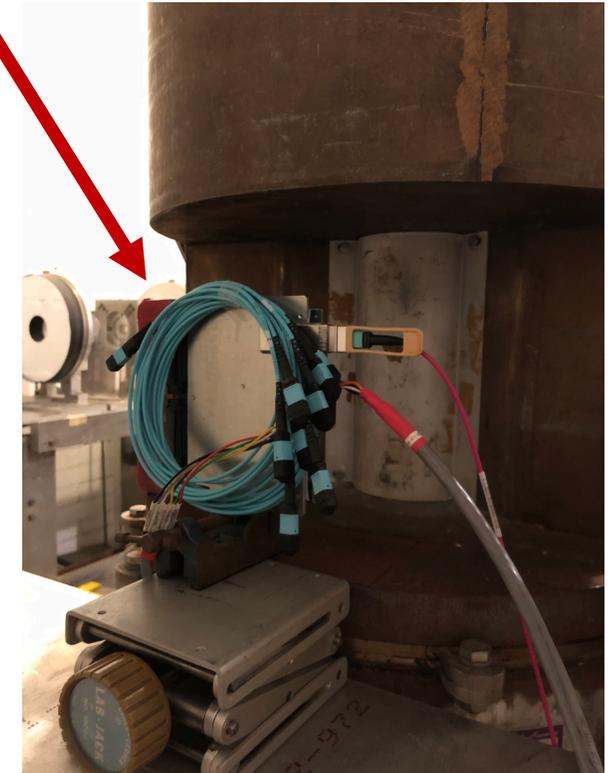
Radiation hardness test

- Radiation hardness requirement for FEE
 - 25krad TID for 5 yrs. We require 100krad hardness.
- Test at ^{60}Co γ source (10krad/hr) at BNL
 - Most of the parts passed the test. Failed parts were replaced with alternate parts later.
 - SAMPA was turned on and data are readout normally. Pedestals are fine. (130nm CMOS is good)



We also performed magnet field test (1.5T), but saw no effect to components (incl optical Tx/Rx)

Manufacturer	Part Number	Description	Test date	Result
TSMC and USP	SAMPA ver4	CSA + Shaper + ADC + DSP	8/2/2019	OK up to 100krad
TI	TPS7A8500RGRT	IC REG LINEAR POS ADJ 4A 20VQFN	7/18/2018	OK up to 100krad
ON Semi	CAT102TDI-GT3	IC VREF SHUNT ADJ TSOT23-5	12/10/2018	dead at 50krad
ON Semi	NUP4114UPXV6T1G	TVS DIODE 5.5VWM 10VC SOT563	8/2/2019	OK up to 100krad
TI	PCA9306DCUR	IC VOLT LEVEL TRANSLATOR US8	8/2/2019	OK up to 100krad
TI	SN74AVC16T245ZQLR	IC BUS TRANSCVR 16BIT 56BGA	8/2/2019	OK up to 100krad
TI	SN74LVC2G04DCKR	IC DUAL INVERTER GATE SC-70-6	8/2/2019	OK up to 100krad
Linear	LTC2991CMS#PBF	IC MONITOR OCTAL 16-MSOP	N/A	
Macronix	MX25L25735FZ2I-10G	IC FLASH 256MBIT 104MHZ 8WSON	12/10/2018	OK at 20krad, dead at 50krad
Abrakon	ASDMB-50.000MHZ-LC-T	OSC MEMS 50.000MHZ CMOS SMD	8/2/2019	OK up to 100krad
Maxim	DS620U+	SENSOR TEMPERATURE I2C 8UMAX	N/A	
Many	EG-2101CA	OSC XO TBD MHZ LVDS 6-SMD, NO LEAD	8/2/2019	OK up to 100krad
Silicon Labs	SI5338B-B-GMR	IC CLK GEN I2C QUAD 24QFN	8/2/2019	OK up to 50krad, dead at 80krad
AVAGO	AFBR-57D7APZ	850nm optical Rx/Tx	7/18/2018	OK up to 100krad



Summary, TODO, and future

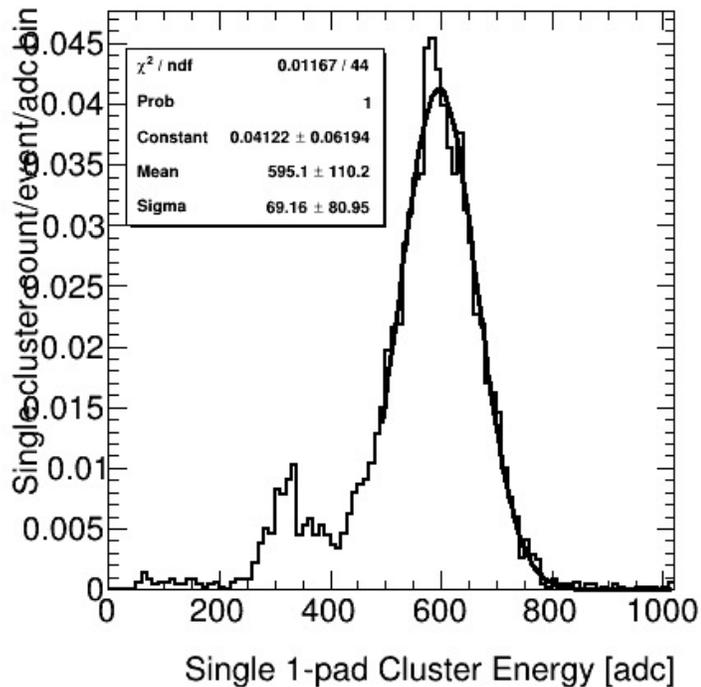
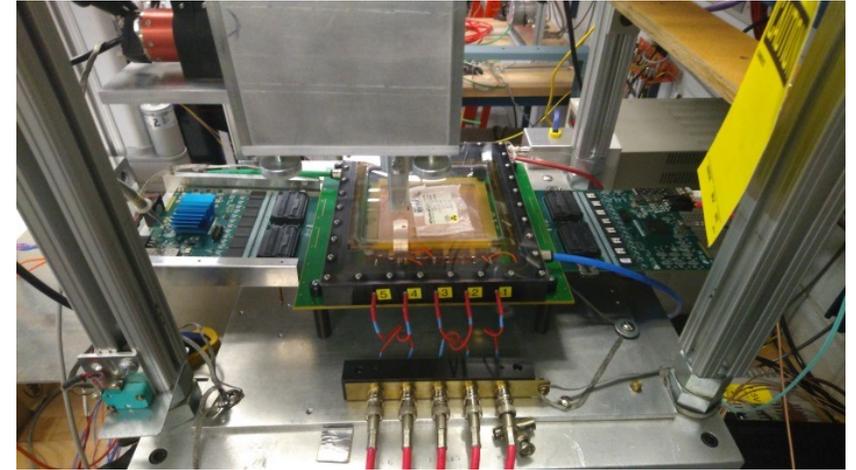
- SAMPA v5 development has been successfully completed
 - ~12k chips have been produced which are more than what sPHENIX TPC FEE will need
 - So far, performance meets our expectation.
- More detailed test of the SAMPA on FEE as well as system integration test are on-going
 - Saturation characteristics (baseline shift)
 - Spark protection test, and several other stress test
- Implementing SEU mitigation for the FEE, mainly for the FPGA
 - SEU for the SAMPA is not critical for operation. It should be less frequent than FPGA.
 - If happens, SAMPA will be reset by FPGA.
- Future of SAMPA
 - TSMC decided to finish producing wafers from MLM masks and the last order with a month ago
 - Some interested parties negotiated with the company at that time.
 - Additional SAMPA chips can still be made but will need to make a new "full" maskset
 - Making full maskset is straightforward. A software can produce it from the existing design file.
 - Cost for the full maskset production is about twice as expensive as MLM maskset.

Backup

FEE prototype around v2 and v4 chips

- Signal from X-ray gun (X-ray fluorescence on ^{55}Mn) to a GEM chamber at has been readout by the prototype FEE (256 channels)

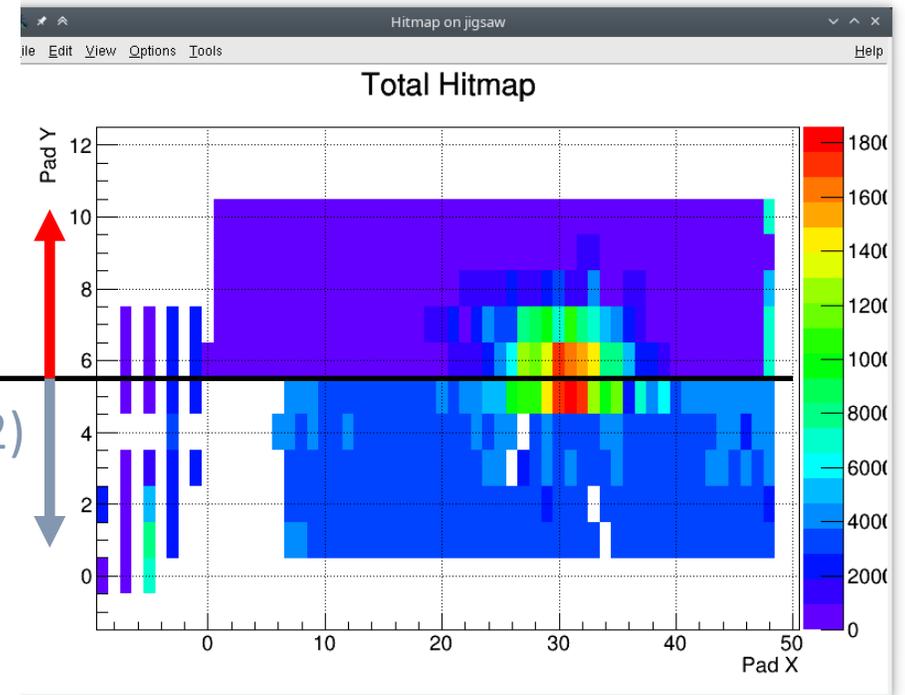
- Hit distribution from ^{55}Fe over two FEEs
 - **Proof-of-principle that DAM properly handles data from multiple-FEEs**
 - **Data taken by John Kuczewski**



Plot made by Jin

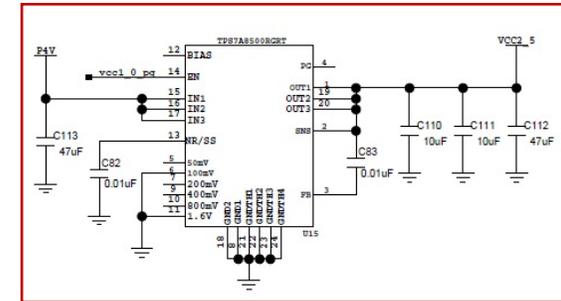
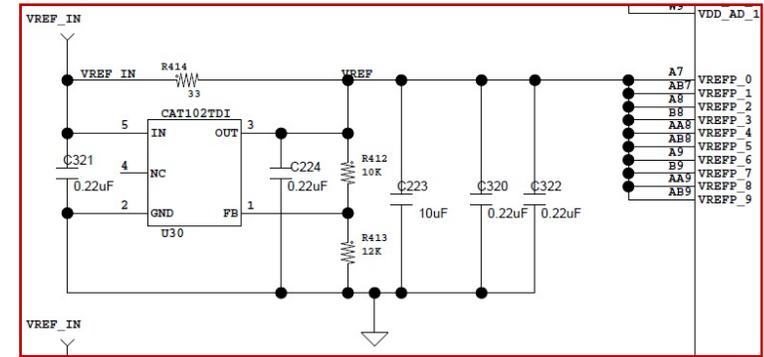
Up: FEE1 (SAMPA v4)

Down: FEE0 (SAMPA v2)

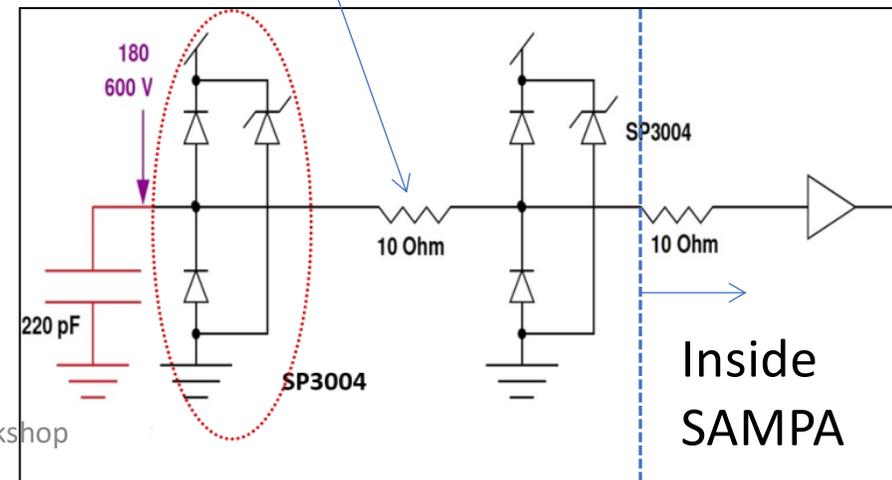


Revision for pre-production board

- ADC reference regulator was replaced
 - CAT102 (one for each SAMPA) with the one used for power regulation (TI TPS7A8500RGRT)
 - One TPS7A8500RGRT takes care of 4 SAMPAs.
 - Decoupling cap will be placed near each SAMPA.
- PLL bypass pads were added for keeping option of removing it at a later time
- New spark protection is implemented.
 - Resistor size is increased from 0201 to 0603.
 - Even ALICE's resistors can be used.
- Largest FPGA, Artix-7 200T (was 100T)
- New SPI flash (EEPROM) for FPGA
 - Cypress S25FL256SAGMFIR01
 - ATLAS confirmed it works upto 40krad

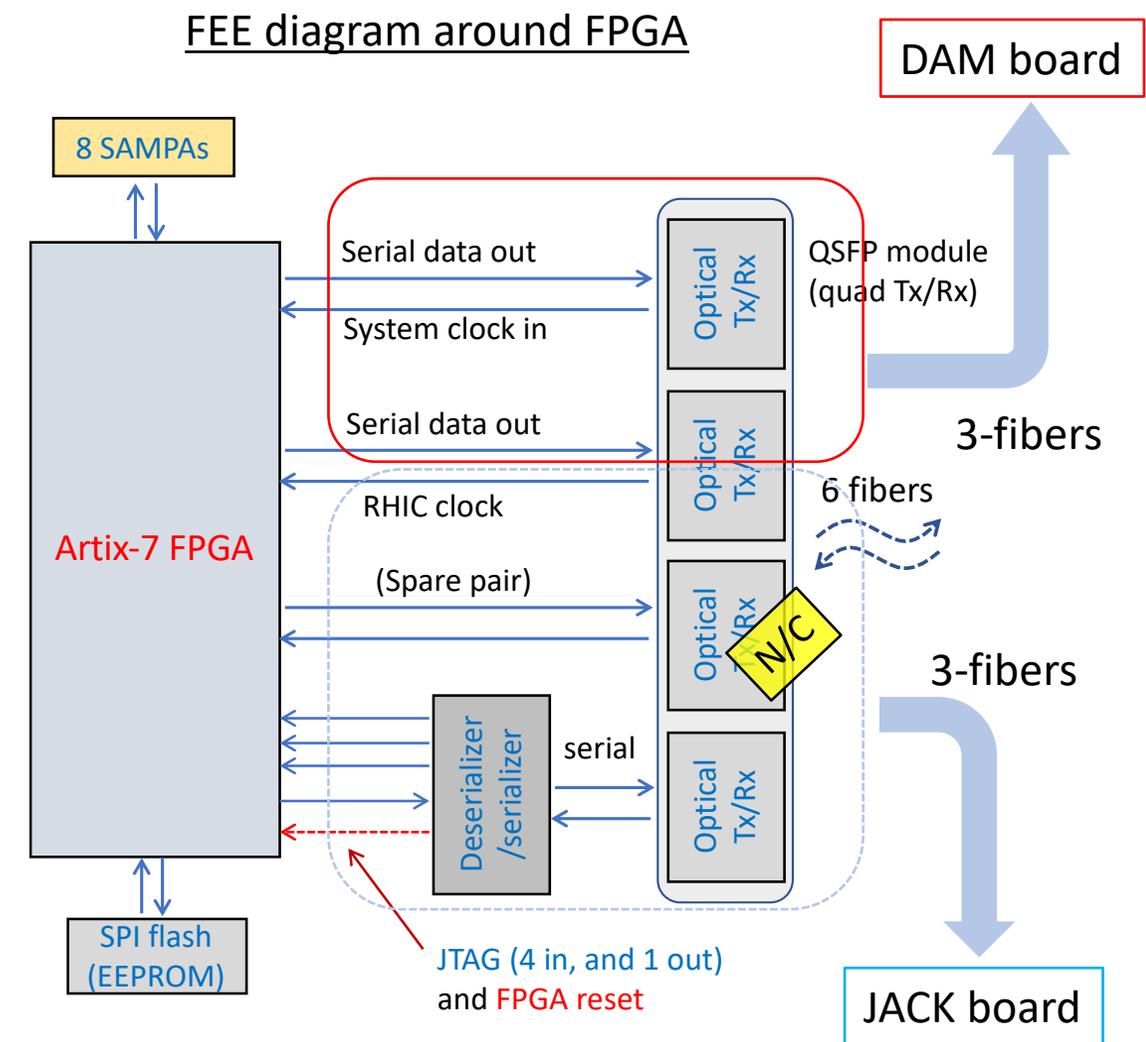


ROHM KTR03EZPF1000
(0603)



JACK development

- Clock:
 - RHIC clock has been recovered through slow-control fiber line now.
 - A dedicated clock line will make the clock synchronizing scheme simpler
- JTAG (over optical fiber):
 - JTAG was primarily for programming FPGA on FEE, in case EEPROM was dead by radiation
 - It turned out that the JTAG connection is very useful for mitigating single event upset (SEU) of the FPGA.
 - FPGA reset without power recycle is implemented only through JTAG



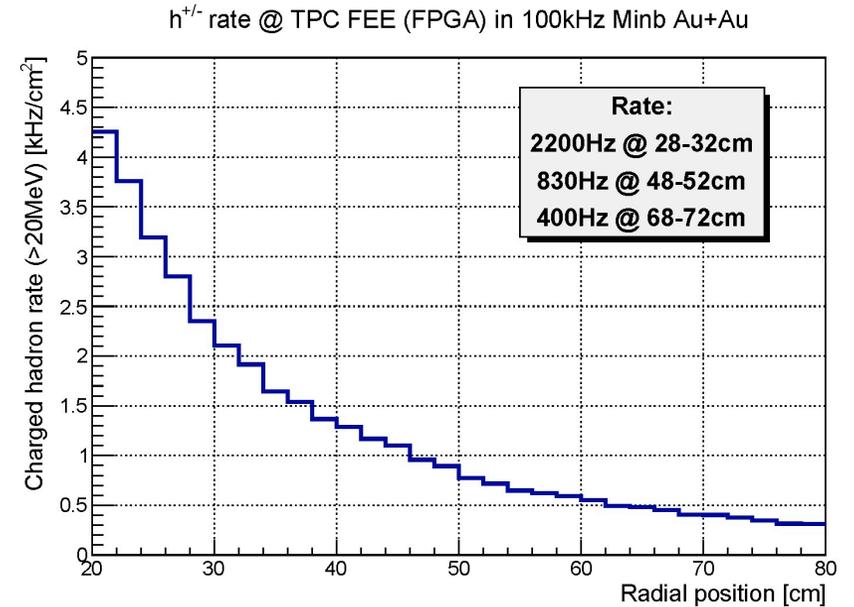
Single event effect on FPGA

- Xilinx Artix-7 7A200T FPGA
- Assuming all CRAM bits are significant
- Used AMPT event generator (Au+Au 200GeV @100KHz) to estimate charged hadron rate at particular positions.
- Triple modular redundancy (TMR), memory scrubbing is implemented

Table 2.7: Soft error for sPHENIX TPC FEE case (using Artix-7 7A200T).

R-position	# of FEE	flux [Hz/cm ²]	error/FEE [s ⁻¹]	error/sector [s ⁻¹]
28-32cm	120	2200	1.6×10^{-6}	1.9×10^{-4}
48-52cm	192	800	5.8×10^{-7}	1.1×10^{-4}
68-72cm	288	400	2.9×10^{-7}	8.6×10^{-5}

One error in 45 minutes as whole TPC



25kRad TID for 5 years.
1.2 10¹² 1MeV-eq n/cm²

